

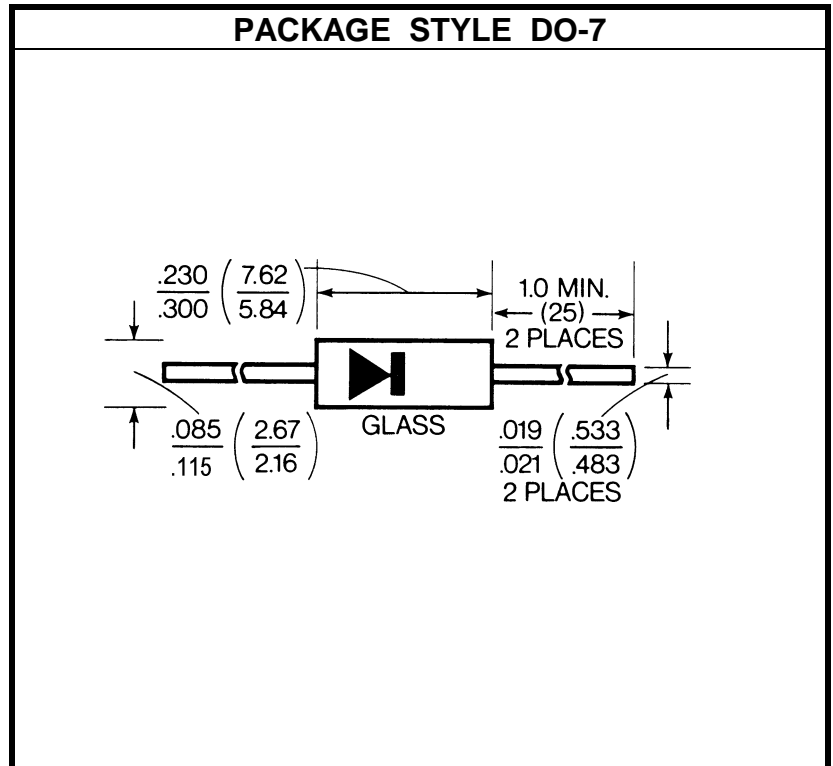
ABRUPT VARACTOR DIODE

DESCRIPTION:

The **ASI 1N5709B** is an Abrupt Varactor Diode, designed for general purpose applications.

MAXIMUM RATINGS

I_R	20 nA
V_R	70 V
P_{DISS}	400 mW @ $T_A = 25\text{ }^\circ\text{C}$
T_J	-65 °C to +175 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	250 °C/W


CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_{BR}	$I_R = 10\text{ }\mu\text{A}$	65			V
I_R	$V_R = 60\text{ V}$			20	nA
		$T_A = 150\text{ }^\circ\text{C}$		20	μA
C_T	$V_R = 4.0\text{ V}$	$f = 1.0\text{ MHz}$	77.9	86.1	pF
C_{T4}/C_{T60}	$V_R = 4.0\text{ V}/V_R = 60\text{ V}$	$f = 1.0\text{ MHz}$	3.2	3.4	--
Q	$V_R = 4.0\text{ V}$	$f = 50\text{ MHz}$	150		--